

GJ3403

P-CHANNEL ENHANCEMENT MODE POWER MOSFET

BVDSS	-30V
RDS(ON)	200mΩ
ID	-10A

Description

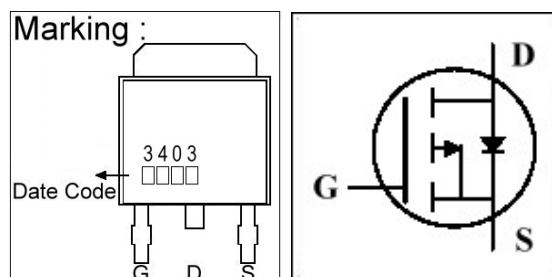
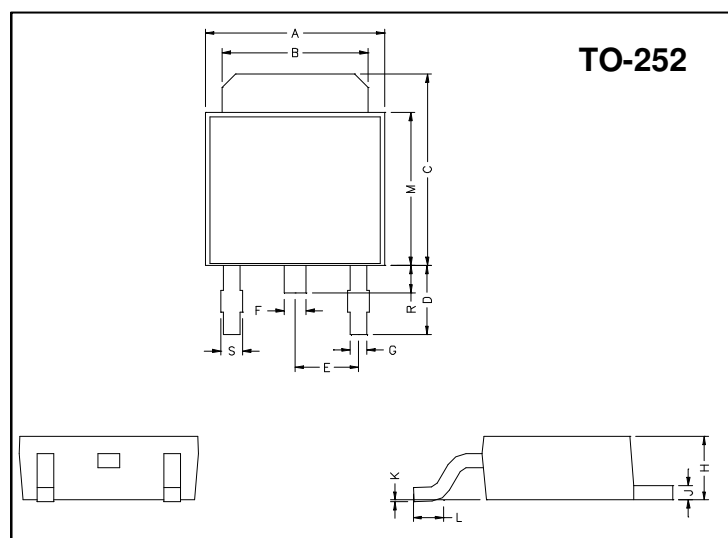
The GJ3403 utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The TO-252 package is universally used for commercial-industrial applications.

Features

- *Simple Drive Requirement
- *Lower Gate Charge
- *Fast Switching

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_D @ T_C=25^\circ C$	-10	A
Continuous Drain Current	$I_D @ T_C=70^\circ C$	-8.6	A
Pulsed Drain Current ¹	I_{DM}	-48	A
Total Power Dissipation	$P_D @ T_C=25^\circ C$	36.7	W
Linear Derating Factor		0.29	W/°C
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	$R_{thj-case}$	3.4	°C/W
Thermal Resistance Junction-ambient Max.	$R_{thj-amb}$	110	°C/W

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} =0, I _D =-250uA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _j	-	-0.1	-	V/°C	Reference to 25°C, I _D =-1mA
Gate Threshold Voltage	V _{GS(th)}	-1.0	-	-3.0	V	V _{DS} =V _{GS} , I _D =-250uA
Forward Transconductance	g _{fs}	-	2	-	S	V _{DS} =-10V, I _D =-6A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	-1	uA	V _{DS} =-30V, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		-	-	-25	uA	V _{DS} =-24V, V _{GS} =0
Static Drain-Source On-Resistance ²	R _{DS(ON)}	-	-	200	mΩ	V _{GS} =-10V, I _D =-6A
		-	-	400		V _{GS} =-4.5V, I _D =-4A
Total Gate Charge ²	Q _g	-	3.8	-	nC	I _D =-6A V _{DS} =-24V V _{GS} =-4.5V
Gate-Source Charge	Q _{gs}	-	1.7	-		
Gate-Drain ("Miller") Charge	Q _{gd}	-	1.6	-		
Turn-on Delay Time ²	T _{d(on)}	-	6.7	-	ns	V _{DS} =-15V I _D =-6A V _{GS} =-10V R _G =2Ω R _D =2.5Ω
Rise Time	T _r	-	20.8	-		
Turn-off Delay Time	T _{d(off)}	-	14.9	-		
Fall Time	T _f	-	4.4	-		
Input Capacitance	C _{iss}	-	217	-	pF	V _{GS} =0V V _{DS} =-25V f=1.0MHz
Output Capacitance	C _{oss}	-	103	-		
Reverse Transfer Capacitance	C _{rss}	-	31	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	-1.2	V	I _S =-1.25A, V _{GS} =0V
Reverse Recovery Time	T _{rr}	-	35	-	ns	I _S =-6A, V _{GS} =0V dI/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	63	-	nC	

Notes: 1. Pulse width limited by Max. junction temperature.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

Characteristics Curve

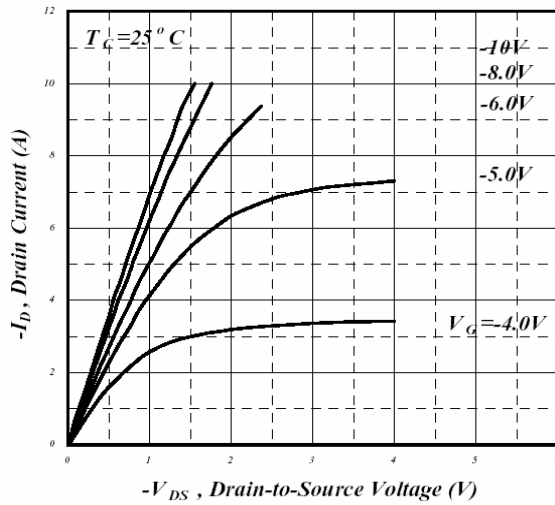


Fig 1. Typical Output Characteristics

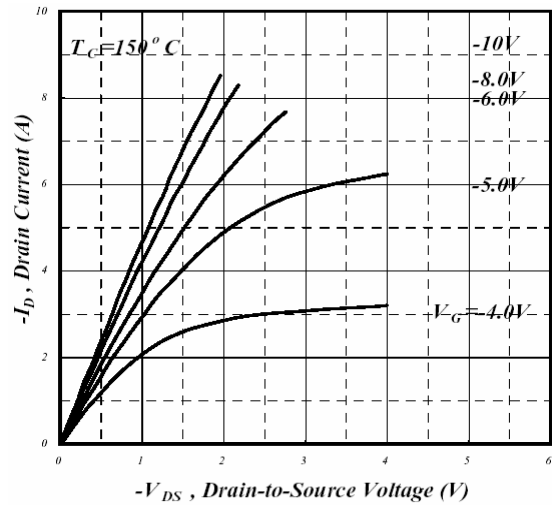


Fig 2. Typical Output Characteristics

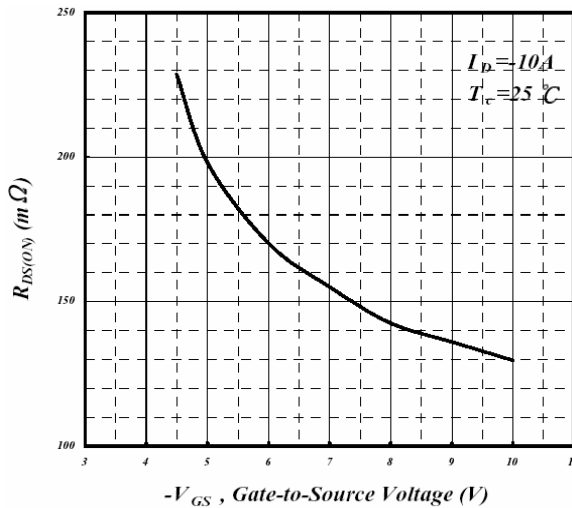


Fig 3. On-Resistance v.s. Gate Voltage

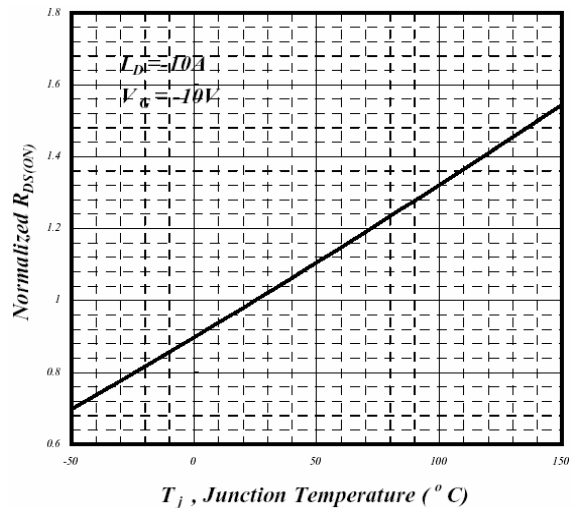


Fig 4. Normalized On-Resistance v.s. Junction Temperature

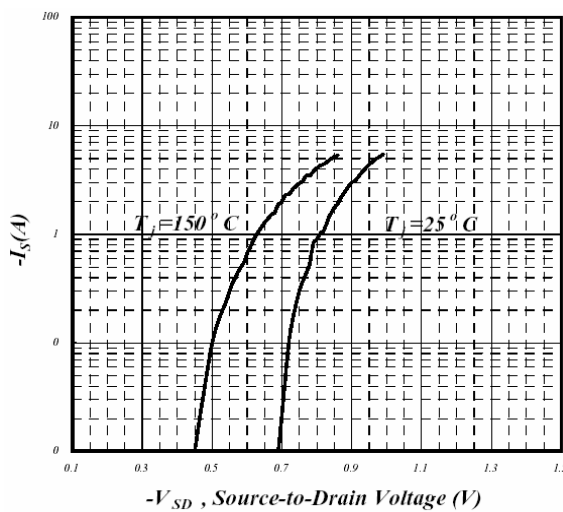


Fig 5. Forward Characteristics of Reverse Diode

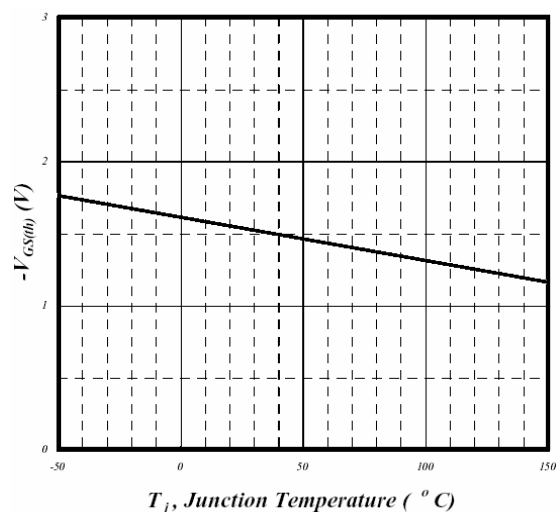


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

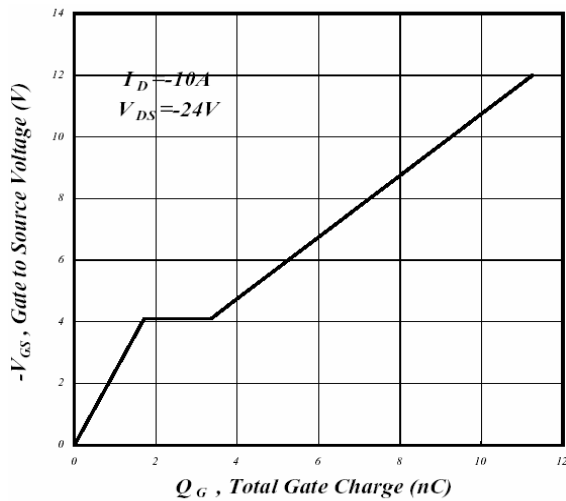


Fig 7. Gate Charge Characteristics

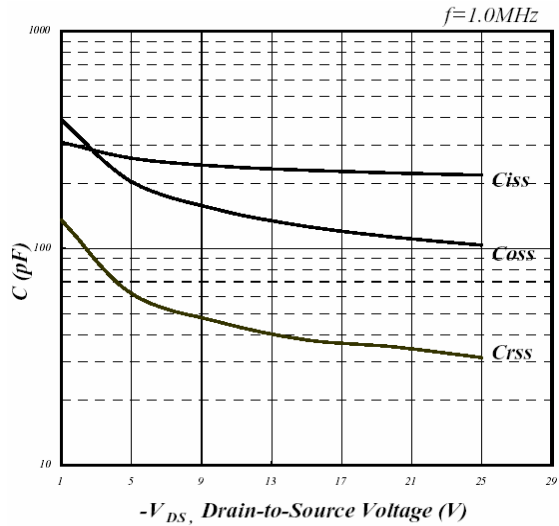


Fig 8. Typical Capacitance Characteristics

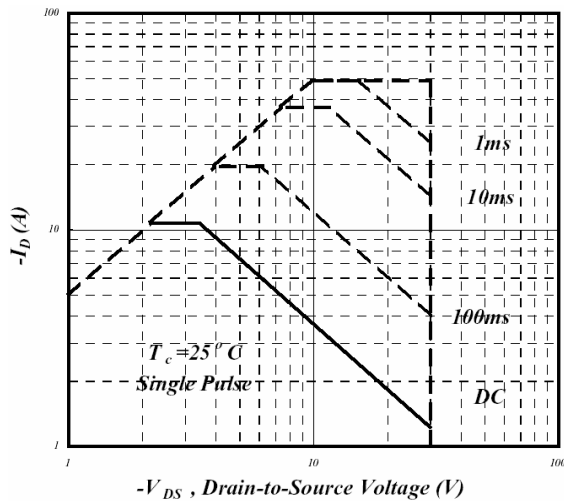


Fig 9. Maximum Safe Operating Area

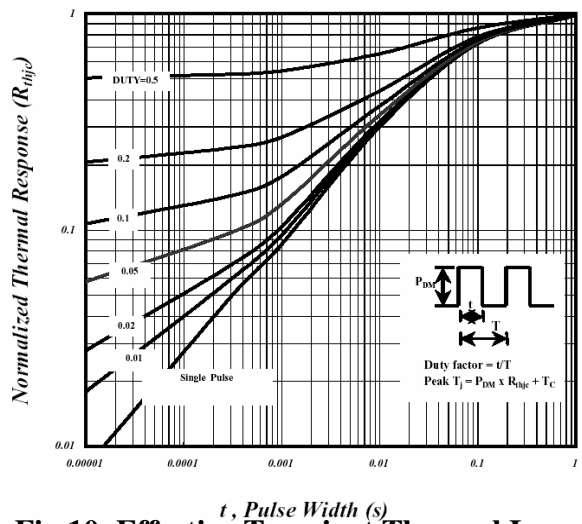


Fig 10. Effective Transient Thermal Impedance

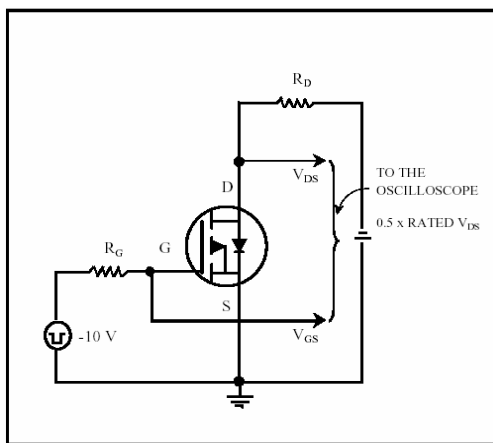


Fig 11. Switching Time Circuit

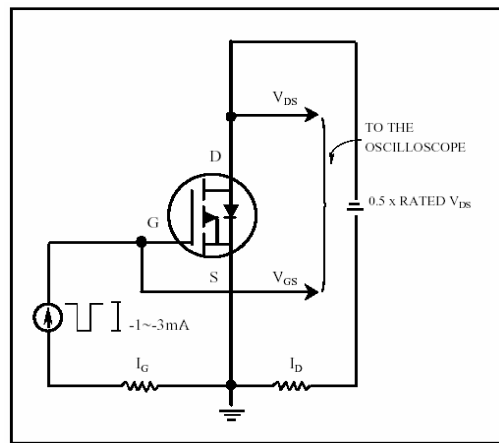


Fig 12. Gate Charge Circuit

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